

Product Summary (typ. @ $V_{GS} = 4.5V$, $T_A = +25^\circ C$)

BV_{SSS}	$R_{SS(ON)}$	Q_g	Q_{gd}	I_S
20V	20m Ω	28.5nC	0.6nC	8.3A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{SS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- Battery managements
- Load switches
- Battery protections

Features

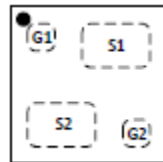
- Common Drain Configuration with:
 $R_{SS(ON)} = 20m\Omega$ to Minimize On-State Losses
 $Q_g = 28.5nC$ for Ultra-Fast Switching
 $V_{GS(TH)} = 0.9V$ typ. for a Low Turn-On Potential
- CSP with Footprint 1.35mm x 1.35mm
- Height = 0.22mm for Low Profile
- ESD Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

Mechanical Data

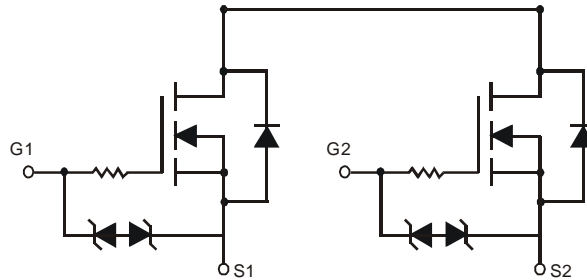
- Package: X4-DSN1313-4
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu or NiAu. Solderable per MIL-STD-202, Method 208e4
- Weight: 0.0026 grams (Approximate)



ESD PROTECTED

X4-DSN1313-4


Top View

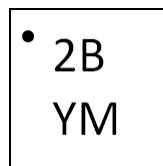


Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN2024LCA4-7	X4-DSN1313-4	3000	Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information
X4-DSN1313-4


2B = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: K = 2023)
 M = Month (ex: 9 = September)

Date Code Key

Year	2020	...	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	H	...	K	L	M	N	P	R	S	T	U	V

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Source Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _S	8.3	A
		T _A = +70°C		6.7	
Continuous Source Current (Note 5) V _{GS} = 2.5V	Steady State	T _A = +25°C	I _S	6.9	A
		T _A = +70°C		5.5	
Pulsed Source Current (Note 6)			I _{SM}	50	A

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Power Dissipation (Note 7)			P _D	1.1	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7)			R _{θJA}	111	°C/W
Power Dissipation (Note 5)			P _D	2.4	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)			R _{θJA}	52	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _S = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{SSS}	—	—	1	μA	V _{SS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	0.5	μA	V _{GS} = 6V, V _{DD} = 0V
		—	—	4		V _{GS} = 10V, V _{DD} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.68	0.9	1.3	V	V _{SS} = V _{GS} , I _S = 250μA
Static Source-Source On-Resistance	R _{SS(ON)}	—	—	21	mΩ	V _{GS} = 6.5V, I _S = 2A
		—	—	23		V _{GS} = 4.5V, I _S = 2A
		—	—	34		V _{GS} = 2.5V, I _S = 2A
Diode Forward Voltage	V _{SS}	—	0.6	1	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	991	—	pF	V _{SS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	137	—		
Reverse Transfer Capacitance	C _{RSS}	—	81	—		
Total Gate Charge	Q _g	—	28.5	—	nC	V _{GS} = 10V, V _{SS} = 10V, I _S = 2A
Gate-Source Charge	Q _{gs}	—	7.4	—		
Gate-Drain Charge	Q _{gd}	—	0.6	—		
Gate Charge at V _{TH}	Q _{G(TH)}	—	4.7	—	ns	V _{SS} = 10V, V _{GS} = 4.5V, R _G = 0Ω, I _S = 2A
Turn-On Delay Time	t _{D(ON)}	—	8.7	—		
Turn-On Rise Time	t _R	—	2.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	17.6	—		
Turn-Off Fall Time	t _F	—	8.4	—		

- Notes:
- Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
 - Repetitive rating, pulse width limited by junction temperature.
 - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

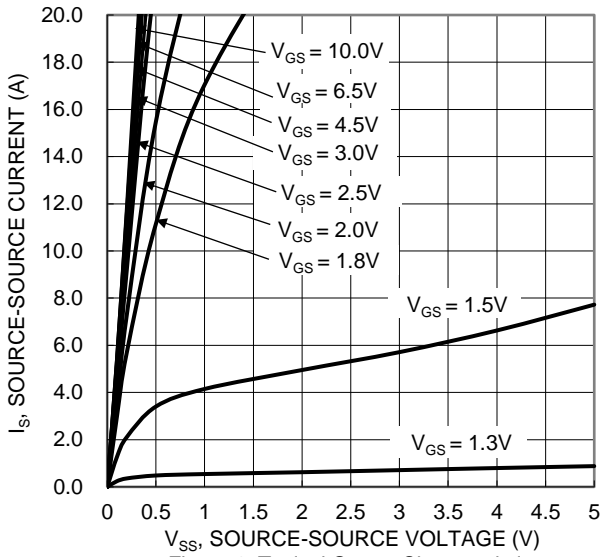


Figure 1. Typical Output Characteristic

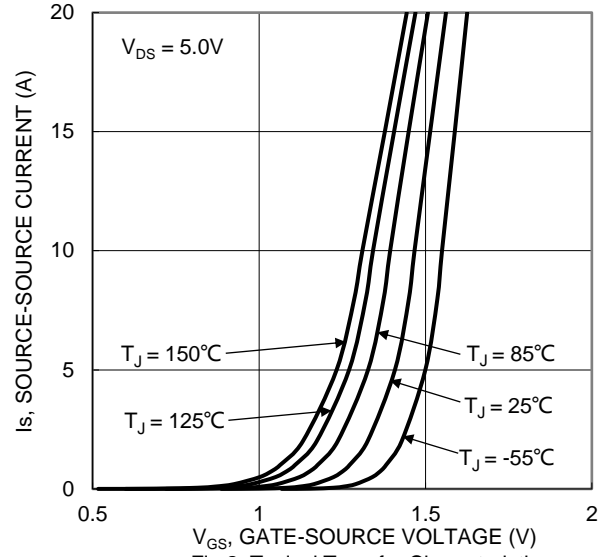


Figure 2. Typical Transfer Characteristic

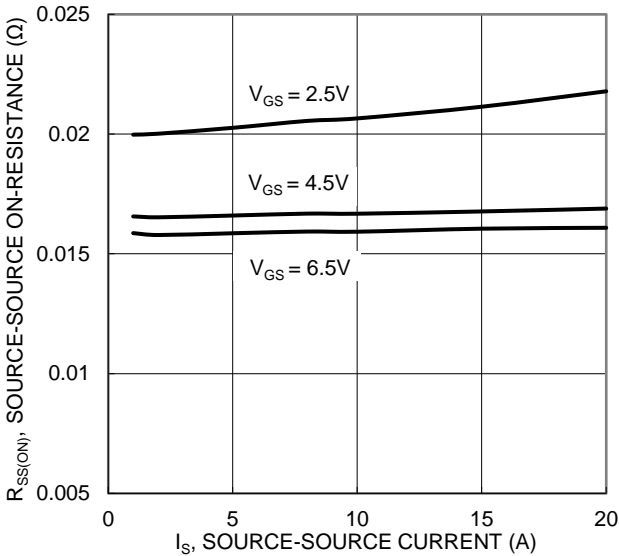


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

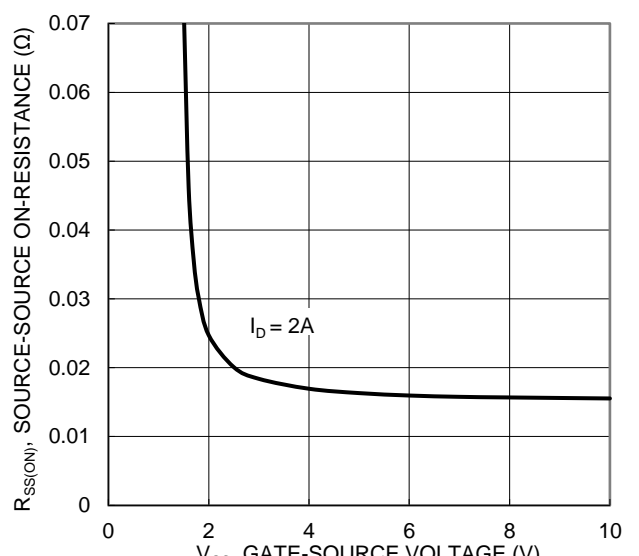


Figure 4. Typical Transfer Characteristic

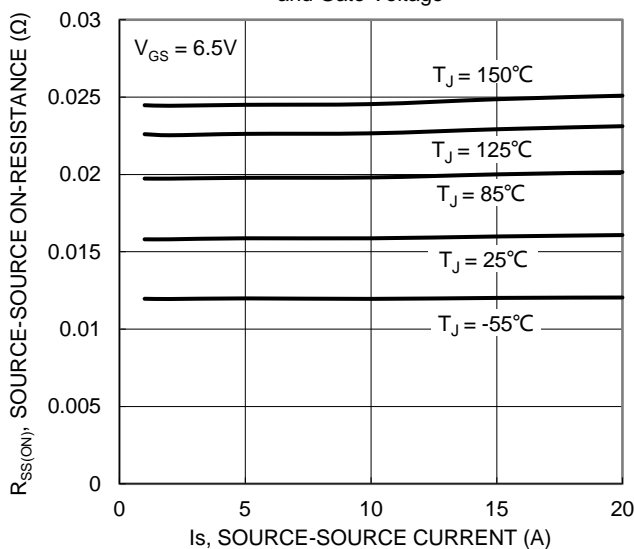


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

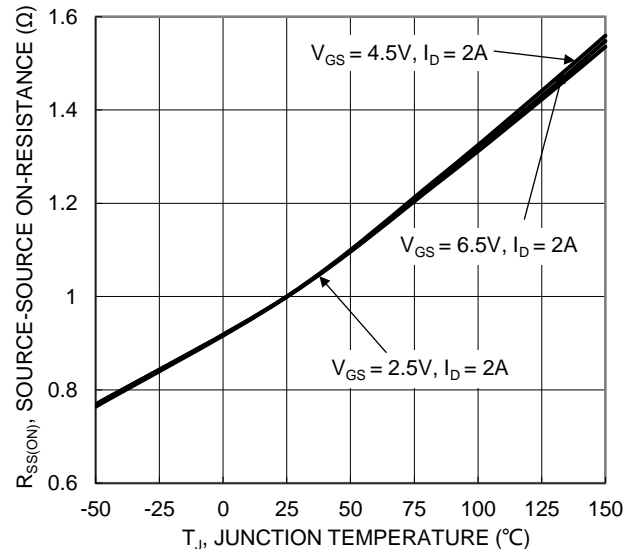
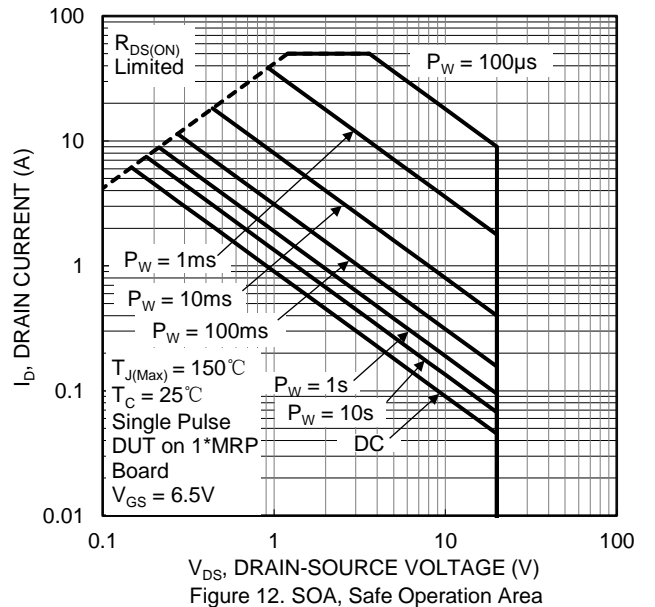
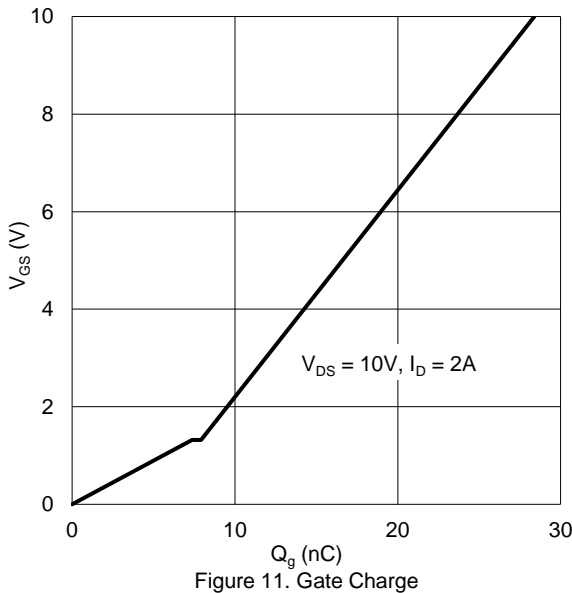
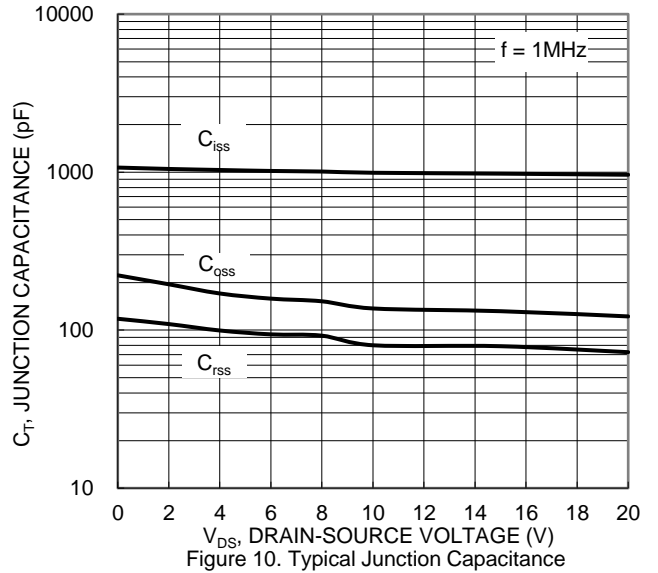
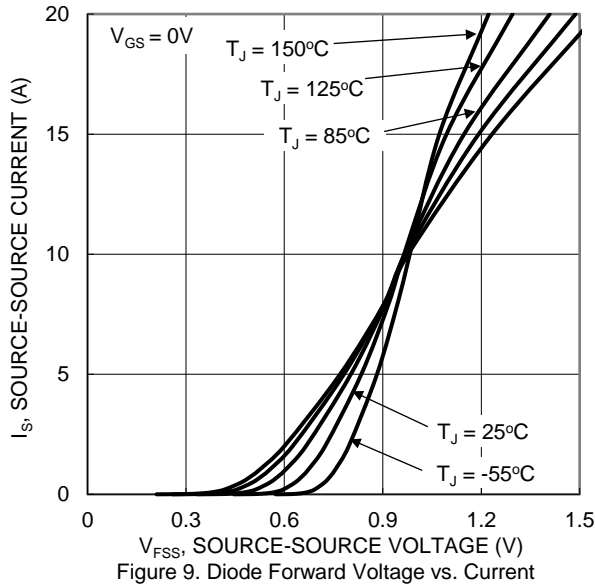
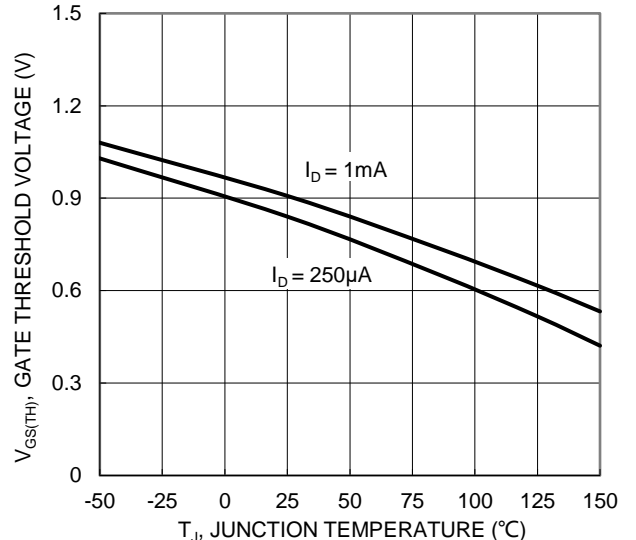
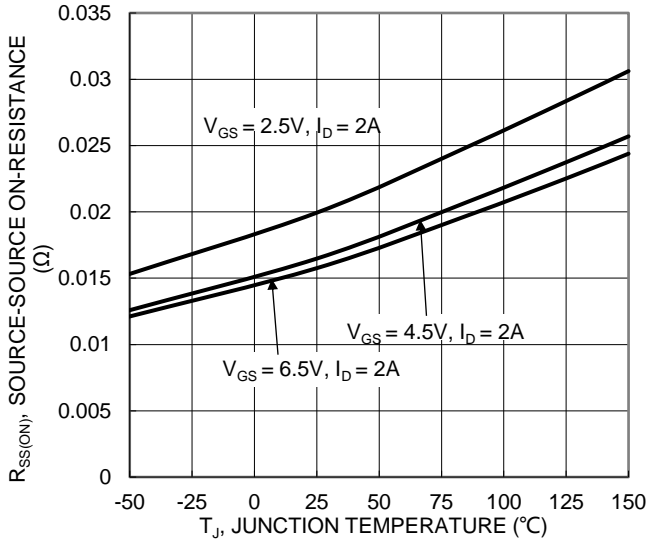


Figure 6. On-Resistance Variation with Temperature



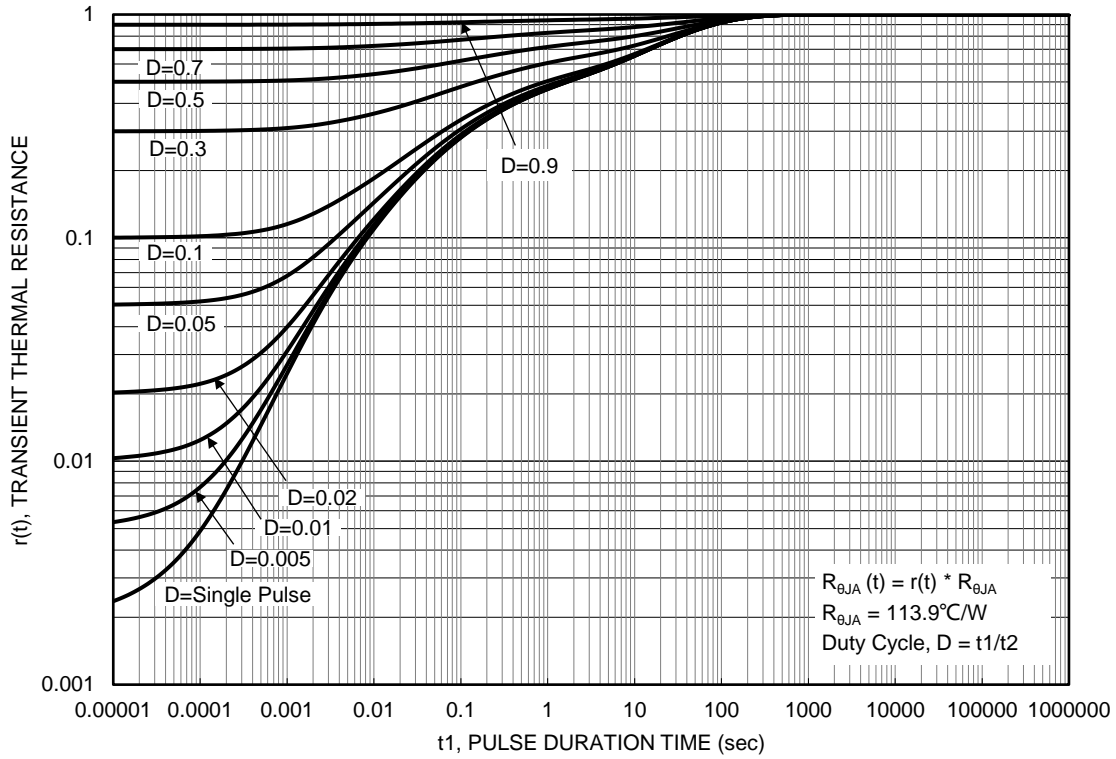
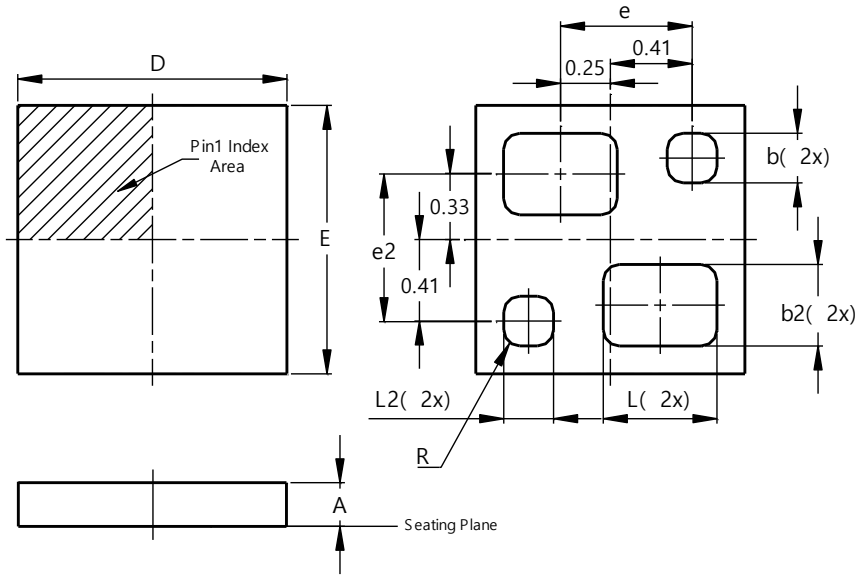


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN1313-4



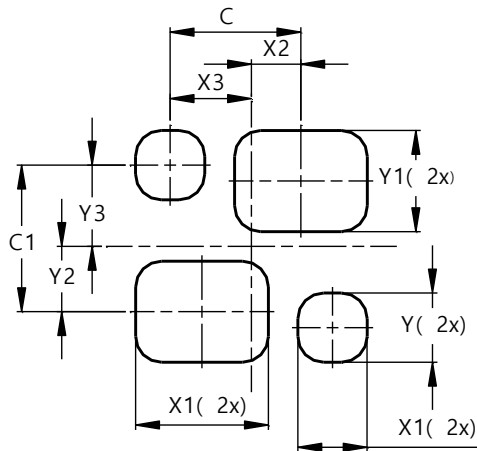
X4-DSN1313-4			
Dim	Min	Max	Typ
A	0.15	0.25	0.20
b	0.24	0.26	0.25
b2	0.40	0.42	0.41
D	1.30	1.40	1.35
E	1.30	1.40	1.35
e	--	--	0.66
e2	--	--	0.74
L	0.56	0.58	0.57
L2	0.24	0.26	0.25
r	--	--	0.08

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN1313-4



Dimensions	Value (in mm)
C	0.66
C1	0.74
X	0.67
X1	0.35
X2	0.25
X3	0.41
Y	0.35
Y1	0.51
Y2	0.33
Y3	0.41

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